



PRO 4|30 AAB EVO

TECHNICAL DATA SHEET

HI-END four-channel Class AB power amplifier

150 W × 4 / 4 Ω 240 W × 4 / 2 Ω
480 W × 2 bridged / 4 Ω

FEATURES

- HI-END Class AB power amplifier.
- AAB technology with distributed local device control.
- Independent local control loops for each output MOSFET.
- Improved thermal stability and bias consistency.
- Optimized behaviour with reactive loudspeaker loads.
- Progressive, more natural clipping behaviour.
- Independent input sensitivity adjustment for each channel via DIP switch.
- Microprocessor-controlled, temperature-dependent fan operation and thermal shutdown protection.
- Perfectly matched for use with Mosconi DSPs.

POWER SUPPLY

Supply voltage	10–16 V
DC-DC converter topology	Unregulated push-pull, 50 kHz
On-board fuse	1 × 150 A
Standby current	< 2 mA
Overall efficiency	> 65%

OUTPUT

RMS output power at 4 Ω	150 W × 4 (62.5 A)
RMS output power at 2 Ω	240 W × 4 (105 A)
Bridged RMS power at 4 Ω	480 W × 2 (105 A)

Current draw shown in parentheses.

SIGNAL INPUT

Low-level input sensitivity	1–8.75 V
Sensitivity adjustment	32 settings via DIP switch Independent for each channel *
Input impedance	20 kΩ

CONNECTIONS

Power supply	Gold-plated terminal block
Speaker output	Gold-plated terminal block
Signal input	4 gold-plated RCA connectors

*SENSITIVITY SETUP

SENSITIVITY CHART

DEFAULT SETTING
2.00V

ON

1 2 3 4 5

1.00		3.00		6.00	
1.25		3.25		6.25	
1.50		3.50		6.50	
1.75		3.75		6.75	
2.00		4.00		7.00	
2.25		4.25		7.25	
2.50		4.50		7.50	
2.75		4.75		7.75	
		5.00		8.00	
		5.25		8.25	
		5.50		8.50	
		5.75		8.75	

CEA-2006-A SPECIFICATIONS

Rated output power	150 W × 4 at 14.4 V, 4 Ω, < 1% THD+N
S/N ratio	> 73 dBA (ref. 1 W at 4 Ω)

THD

THD at 4 Ω, stereo	< 0.05% (1 kHz, 90% rated power)
THD at 2 Ω, stereo	< 0.055% (1 kHz, 90% rated power)

OTHER ELECTRICAL CHARACTERISTICS

Mute delay	3 s
Secondary voltages (VDD / SERV / DRIVE)	±45.5 / ±15.6 / ±15 V
Channel bias	Dynamic
Idle current (no signal, 14.4 V)	6.5 A
Thermal shutdown current	7 A
Battery-to-secondary ground decoupling	1 kΩ
Battery-to-chassis ground decoupling	100 mA PTC (approx. 7 Ω)
Bandwidth (–3 dB at 1 W)	20 Hz–20 kHz
S/N ratio (10 Hz–22 kHz, ref. rated power)	100 dB (A-weighted)
Equivalent input noise (10 Hz–22 kHz)	< 7.5 μV (A-weighted)
Channel separation (ref. 10 W)	> 66 dB
Fan on/off temperature	50 / 45 °C
Thermal shutdown/restart	90 / 70 °C
Damping factor at 4 Ω	> 105
Start-stop operation	Down to 7.5 V for up to 300 ms
Microcontroller	Atmel processor

PCB

Base material	FR4 (135 °C)
Solder mask	Matte black
Number of layers	4
Copper thickness	70 μm
Surface finish	Gold

APPEARANCE

Dimensions	500 × 205 × 55 mm
Weight	5.1 kg
Finish	Black / Titanium